

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Original): A semiconductor device comprising:

a semiconductor chip which includes a circuit element, a first wiring and an electrode pad, wherein the circuit element includes an electronic element, and wherein the first wiring is electrically connected between the circuit element to the electrode pad;

an insulating layer formed on the semiconductor chip, wherein the insulating layer has an opening which is aligned over the electrode pad;

an external terminal formed on the insulating layer;

a second wiring formed on the insulating layer, wherein the second wiring electrically connects the electrode pad to the external terminal via the opening; and

a shielding film located in a same plane as the first wiring and interposed between the electronic element and the second wiring.

Claim 2 (Original): The semiconductor device according to claim 1, wherein the electronic element includes a capacitor, and wherein the shielding film completely overlaps the capacitor.

Claim 3 (Original): The semiconductor device according to claim 1, wherein the shielding film is a metal and is connected to a ground voltage.

Claim 4 (Original): The semiconductor device according to claim 1, wherein the first wiring is located on a multilevel interconnection structure having a plurality of interconnection layers, and wherein the shielding film is formed in the interconnection layers.

Claim 5 (Original): The semiconductor device according to claim 1, wherein the electrode pad is located in a peripheral region of the semiconductor device, and wherein the external terminal is located in a central region of the semiconductor device.

Claim 6 (Original): The semiconductor device according to claim 2, wherein the circuit element comprises a voltage controlled oscillator which includes the capacitor.

Claim 7 (Original): The semiconductor device according to claim 6, wherein the voltage controlled oscillator generates a signal having a frequency of at least 300 MHz.

Claim 8 (Original): The semiconductor device according to claim 1, wherein the first wiring and the shielding film are a same material.

Claim 9 (Original): The semiconductor device according to claim 1, wherein the circuit element includes an analog circuit which is located under the shielding film.

Claim 10 (Currently Amended): The semiconductor device according to claim 1, further comprising a sealing resin which seals the ~~[[first]]~~ second wiring, wherein a top surface of the external terminal is exposed from the sealing resin.

Claim 11 (Original): The semiconductor device according to claim 1, wherein the external terminal includes a projection and an extended portion, wherein the extended portion extends from the second wiring to a top surface of the projection.

Claim 12 (Original): The semiconductor device according to claim 10, further comprising a post electrode which connects the second wiring to the external terminal.

Claims 13-17 (Canceled)

Claim 18 (Original): A semiconductor device comprising:

- a semiconductor chip;
- a first inductor formed on the semiconductor chip;
- a first insulating layer formed on the semiconductor chip and the first inductor;
- a first shielding film formed on the first insulating layer;

a second insulating layer formed on the first insulating layer and the first shielding film;

a second shielding film formed on the second insulating layer;

a third insulating layer formed on the second insulating layer and the second shielding film; and

a second inductor and an external terminal formed on the third insulating layer;

wherein the first inductor is located under the first shielding film and the second shielding film is located under the second inductor.

Claim 19 (Original): The semiconductor device according to claim 18, wherein the first shielding film and the second shielding film are a magnetic material.